



## STB55NF03L

N-CHANNEL 30V - 0.01Ω - 55A D<sup>2</sup>PAK

STripFET™ POWER MOSFET

| TYPE       | V <sub>DSS</sub> | R <sub>DS(on)</sub> | I <sub>D</sub> |
|------------|------------------|---------------------|----------------|
| STB55NF03L | 30 V             | <0.013 Ω            | 55 A           |

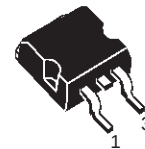
- TYPICAL R<sub>DS(on)</sub> = 0.01 Ω
- OPTIMIZED FOR HIGH SWITCHING OPERATIONS
- LOW GATE CHARGE
- LOGIC LEVEL GATE DRIVE

### DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

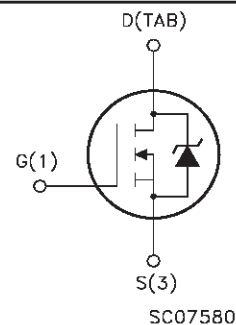
- LOW VOLTAGE DC-DC CONVERTERS
- HIGH CURRENT, HIGH SPEED SWITCHING
- HIGH EFFICIENCY SWITCHING CIRCUITS



**D<sup>2</sup>PAK  
TO-263  
(suffix "T4")**

ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

| Symbol              | Parameter                                            | Value      | Unit |
|---------------------|------------------------------------------------------|------------|------|
| V <sub>DS</sub>     | Drain-source Voltage (V <sub>GS</sub> = 0)           | 30         | V    |
| V <sub>DGR</sub>    | Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)         | 30         | V    |
| V <sub>GS</sub>     | Gate- source Voltage                                 | ±20        | V    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>C</sub> = 25°C  | 55         | A    |
| I <sub>D</sub>      | Drain Current (continuous) at T <sub>C</sub> = 100°C | 39         | A    |
| I <sub>DM</sub> (●) | Drain Current (pulsed)                               | 220        | A    |
| P <sub>tot</sub>    | Total Dissipation at T <sub>C</sub> = 25°C           | 80         | W    |
|                     | Derating Factor                                      | 0.53       | W/°C |
| T <sub>stg</sub>    | Storage Temperature                                  | -60 to 175 | °C   |
| T <sub>j</sub>      | Max. Operating Junction Temperature                  | 175        | °C   |

(●)Pulse width limited by safe operating area.

## STB55NF03L

### THERMAL DATA

|                |                                                |     |       |               |
|----------------|------------------------------------------------|-----|-------|---------------|
| $R_{thj-case}$ | Thermal Resistance Junction-case               | Max | 1.875 | $^{\circ}C/W$ |
| $R_{thj-amb}$  | Thermal Resistance Junction-ambient            | Max | 62.5  | $^{\circ}C/W$ |
| $R_{thc-sink}$ | Thermal Resistance Case-sink                   | Typ | 0.5   | $^{\circ}C/W$ |
| $T_j$          | Maximum Lead Temperature For Soldering Purpose |     | 300   | $^{\circ}C$   |

### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$ unless otherwise specified)

#### OFF

| Symbol        | Parameter                                        | Test Conditions                                                                   | Min. | Typ. | Max.      | Unit               |
|---------------|--------------------------------------------------|-----------------------------------------------------------------------------------|------|------|-----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source Breakdown Voltage                   | $I_D = 250 \mu A$ $V_{GS} = 0$                                                    | 30   |      |           | V                  |
| $I_{DSS}$     | Zero Gate Voltage Drain Current ( $V_{GS} = 0$ ) | $V_{DS} = \text{Max Rating}$<br>$V_{DS} = \text{Max Rating}$ $T_C = 125^{\circ}C$ |      |      | 1<br>10   | $\mu A$<br>$\mu A$ |
| $I_{GSS}$     | Gate-body Leakage Current ( $V_{DS} = 0$ )       | $V_{GS} = \pm 20 V$                                                               |      |      | $\pm 100$ | nA                 |

#### ON (\*)

| Symbol       | Parameter                         | Test Conditions                                                   | Min. | Typ.          | Max.           | Unit                 |
|--------------|-----------------------------------|-------------------------------------------------------------------|------|---------------|----------------|----------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS} = V_{GS}$ $I_D = 250 \mu A$                               | 1    |               | 2.5            | V                    |
| $I_{DS(on)}$ | Static Drain-source On Resistance | $V_{GS} = 10 V$ $I_D = 27.5 A$<br>$V_{GS} = 4.5 V$ $I_D = 27.5 A$ |      | 0.01<br>0.015 | 0.013<br>0.021 | $\Omega$<br>$\Omega$ |
| $I_{D(on)}$  | On State Drain Current            | $V_{DS} > I_{D(on)} \times R_{DS(on)max}$<br>$V_{GS} = 10 V$      | 55   |               |                | A                    |

#### DYNAMIC

| Symbol                              | Parameter                                                                | Test Conditions                                             | Min. | Typ.               | Max. | Unit           |
|-------------------------------------|--------------------------------------------------------------------------|-------------------------------------------------------------|------|--------------------|------|----------------|
| $g_{fs}$ (*)                        | Forward Transconductance                                                 | $V_{DS} > I_{D(on)} \times R_{DS(on)max}$<br>$I_D = 27.5 A$ |      | 40                 |      | S              |
| $C_{iss}$<br>$C_{oss}$<br>$C_{rss}$ | Input Capacitance<br>Output Capacitance<br>Reverse Transfer Capacitances | $V_{DS} = 25V$ $f = 1 MHz$ $V_{GS} = 0$                     |      | 1450<br>390<br>150 |      | pF<br>pF<br>pF |

## ELECTRICAL CHARACTERISTICS (continued)

## SWITCHING ON

| Symbol                        | Parameter                                                    | Test Conditions                                                                                                             | Min. | Typ.           | Max. | Unit           |
|-------------------------------|--------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------|------|----------------|------|----------------|
| $t_{d(on)}$<br>$t_r$          | Turn-on Delay Time<br>Rise Time                              | $V_{DD} = 15\text{ V}$ $I_D = 27.5\text{ A}$<br>$R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$<br>(see test circuit, Figure 3) |      | 25<br>280      |      | ns<br>ns       |
| $Q_g$<br>$Q_{gs}$<br>$Q_{gd}$ | Total Gate Charge<br>Gate-Source Charge<br>Gate-Drain Charge | $V_{DD}=24\text{V}$ $I_D=55\text{A}$ $V_{GS}=4.5\text{V}$                                                                   |      | 25<br>11<br>12 | 35   | nC<br>nC<br>nC |

## SWITCHING OFF

| Symbol                | Parameter                        | Test Conditions                                                                                                             | Min. | Typ.     | Max. | Unit     |
|-----------------------|----------------------------------|-----------------------------------------------------------------------------------------------------------------------------|------|----------|------|----------|
| $t_{d(off)}$<br>$t_f$ | turn-off Delay Time<br>Fall Time | $V_{DD} = 15\text{ V}$ $I_D = 27.5\text{ A}$<br>$R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$<br>(see test circuit, Figure 3) |      | 40<br>60 |      | ns<br>ns |

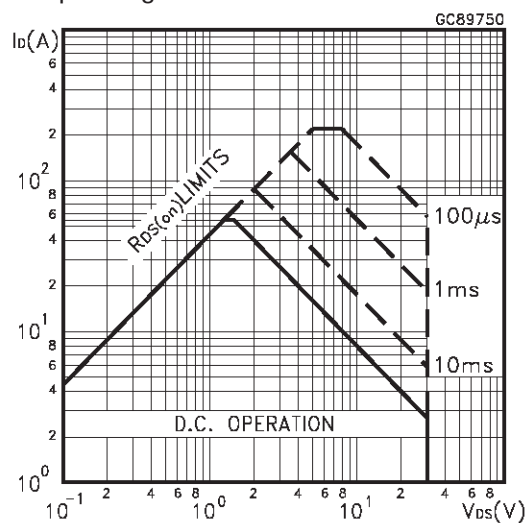
## SOURCE DRAIN DIODE

| Symbol                            | Parameter                                                                    | Test Conditions                                                                                                                                       | Min. | Typ.                | Max.      | Unit          |
|-----------------------------------|------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------|------|---------------------|-----------|---------------|
| $I_{SD}$<br>$I_{SDM}(\bullet)$    | Source-drain Current<br>Source-drain Current (pulsed)                        |                                                                                                                                                       |      |                     | 55<br>220 | A<br>A        |
| $V_{SD}(\ast)$                    | Forward On Voltage                                                           | $I_{SD} = 55\text{ A}$ $V_{GS} = 0$                                                                                                                   |      |                     | 1.3       | V             |
| $t_{rr}$<br>$Q_{rr}$<br>$I_{RRM}$ | Reverse Recovery Time<br>Reverse Recovery Charge<br>Reverse Recovery Current | $I_{SD} = 55\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$<br>$V_{DD} = 15\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$<br>(see test circuit, Figure 5) |      | 45<br>52<br>11.52.3 |           | ns<br>nC<br>A |

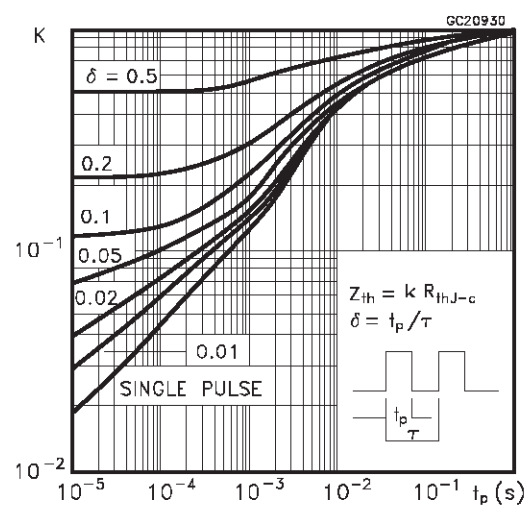
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

( $\bullet$ ) Pulse width limited by safe operating area.

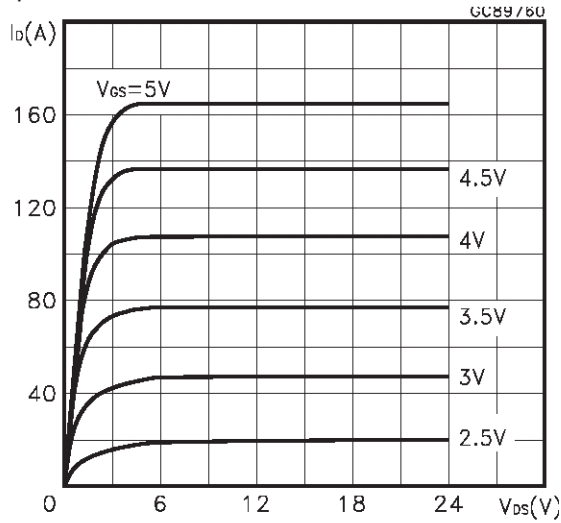
## Safe Operating Area



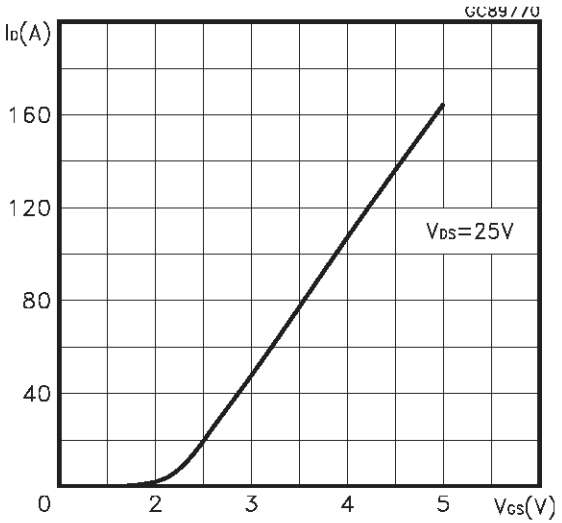
## Thermal Impedance



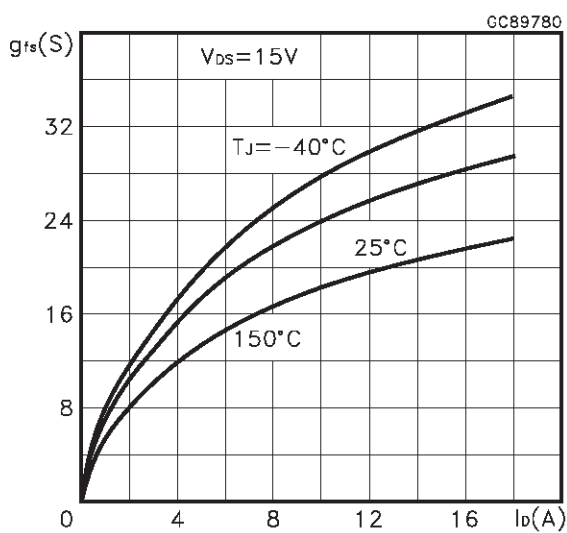
Output Characteristics



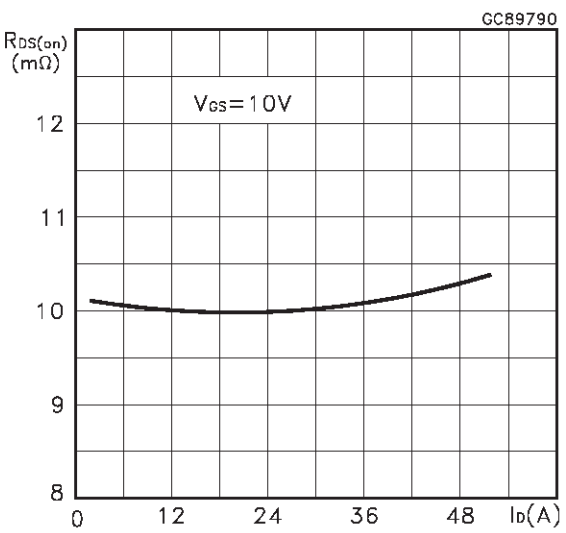
Transfer Characteristics



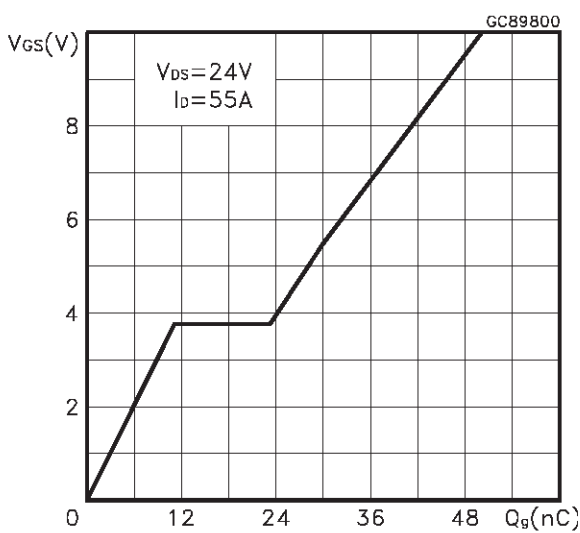
Transconductance



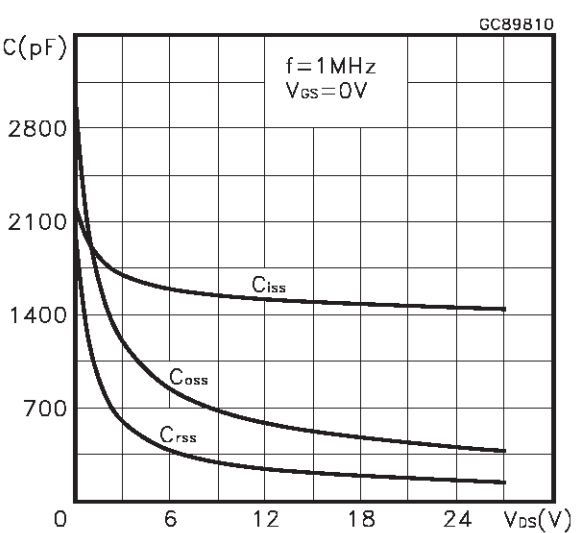
Static Drain-source On Resistance



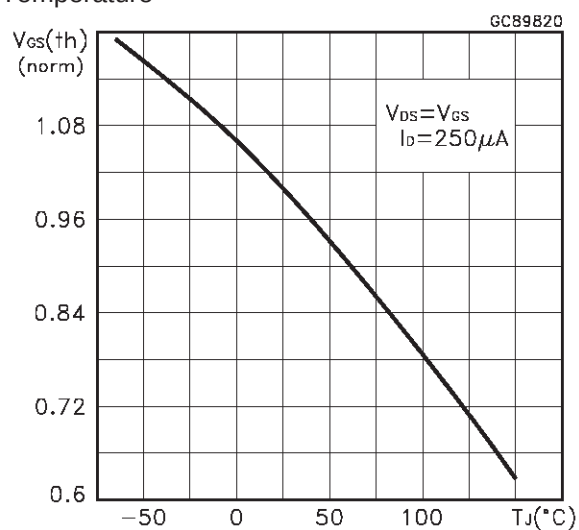
Gate Charge vs Gate-source Voltage



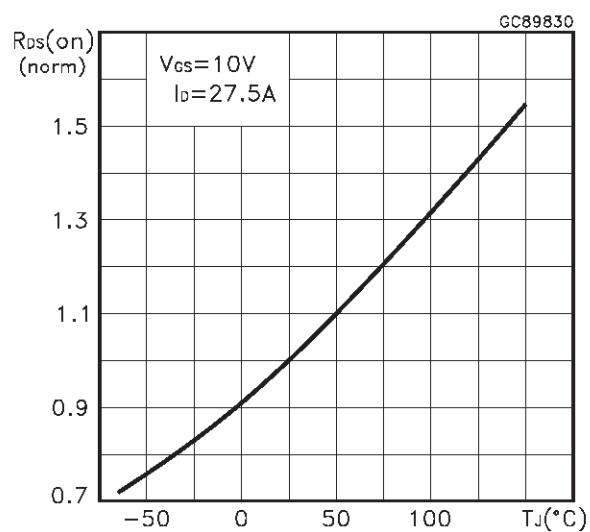
Capacitance Variations



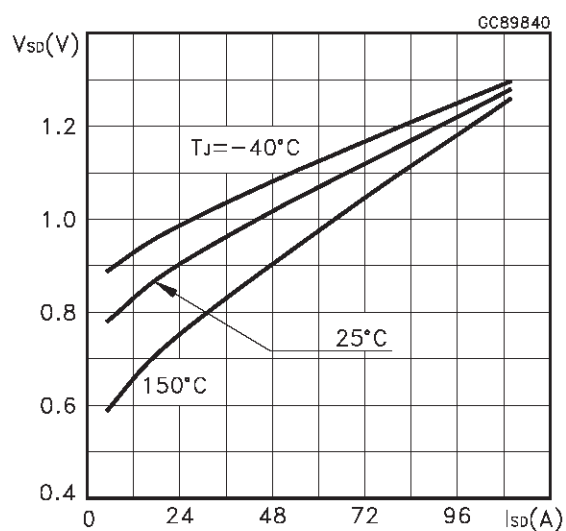
Normalized Gate Threshold Voltage vs Temperature



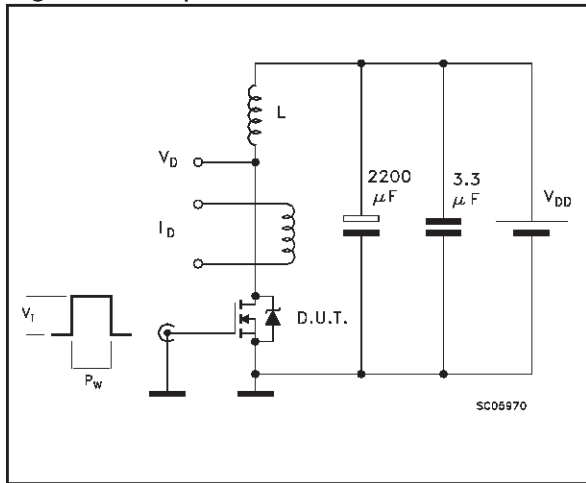
Normalized On Resistance vs Temperature



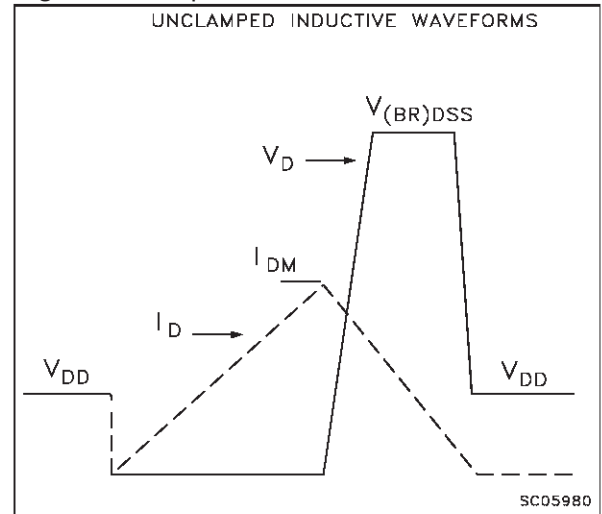
Source-drain Diode Forward Characteristics



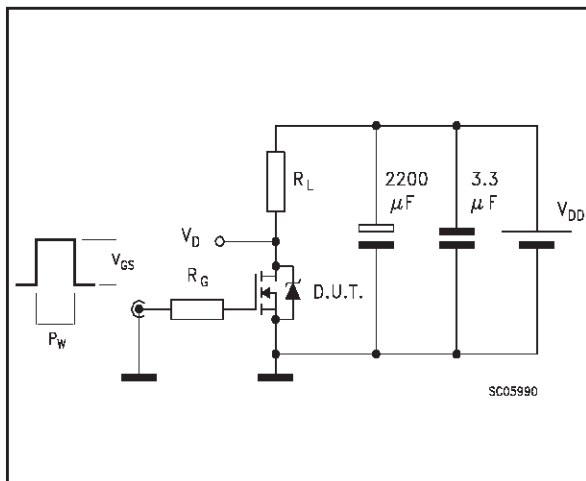
**Fig. 1: Unclamped Inductive Load Test Circuit**



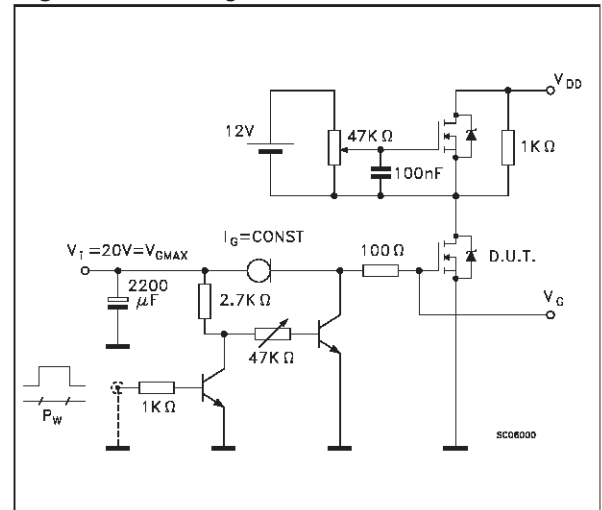
**Fig. 2: Unclamped Inductive Waveform**



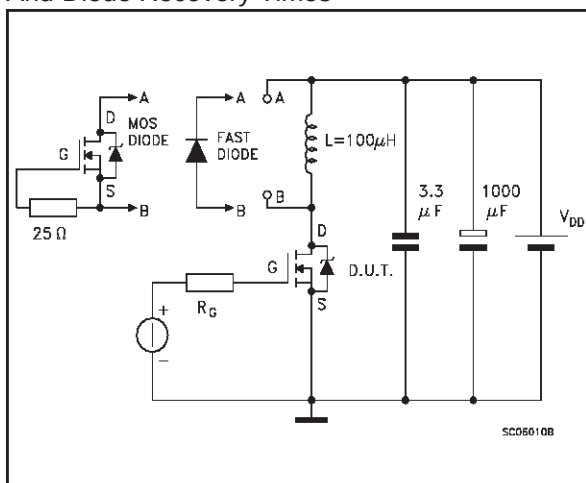
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

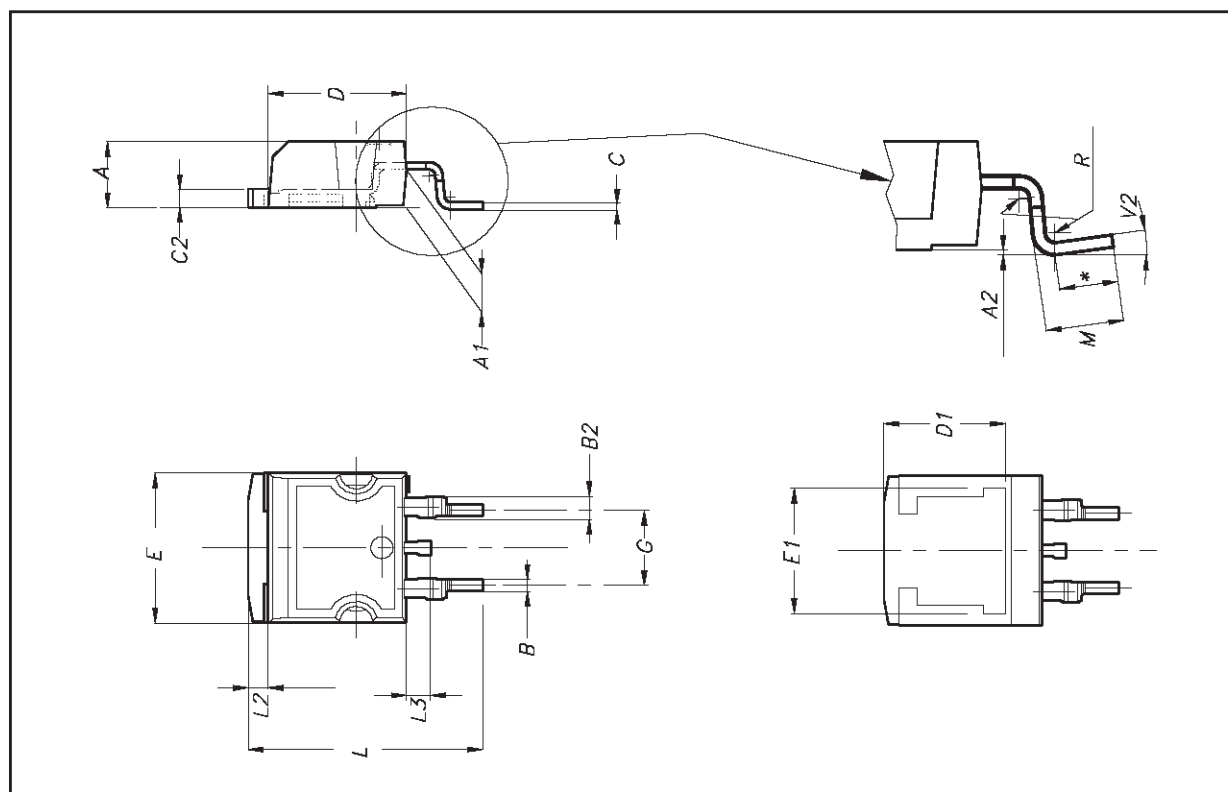


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



D<sup>2</sup>PAK MECHANICAL DATA

| DIM. | mm.  |     |       | inch  |       |       |
|------|------|-----|-------|-------|-------|-------|
|      | MIN. | TYP | MAX.  | MIN.  | TYP.  | MAX.  |
| A    | 4.4  |     | 4.6   | 0.173 |       | 0.181 |
| A1   | 2.49 |     | 2.69  | 0.098 |       | 0.106 |
| A2   | 0.03 |     | 0.23  | 0.001 |       | 0.009 |
| B    | 0.7  |     | 0.93  | 0.027 |       | 0.036 |
| B2   | 1.14 |     | 1.7   | 0.044 |       | 0.067 |
| C    | 0.45 |     | 0.6   | 0.017 |       | 0.023 |
| C2   | 1.23 |     | 1.36  | 0.048 |       | 0.053 |
| D    | 8.95 |     | 9.35  | 0.352 |       | 0.368 |
| D1   |      | 8   |       |       | 0.315 |       |
| E    | 10   |     | 10.4  | 0.393 |       |       |
| E1   |      | 8.5 |       |       | 0.334 |       |
| G    | 4.88 |     | 5.28  | 0.192 |       | 0.208 |
| L    | 15   |     | 15.85 | 0.590 |       | 0.625 |
| L2   | 1.27 |     | 1.4   | 0.050 |       | 0.055 |
| L3   | 1.4  |     | 1.75  | 0.055 |       | 0.068 |
| M    | 2.4  |     | 3.2   | 0.094 |       | 0.126 |
| R    |      | 0.4 |       |       | 0.015 |       |
| V2   | 0°   |     | 8°    |       |       |       |



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